GL05T to GL24T

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ABSOLUTE MAXIMUM RATINGS GL05T						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	8/20 μs	I _{PPM}	17	А		
Peak pulse power	8/20 µs waveform	P _{PP}	300	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 8	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 15	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GL12T						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	8/20 μs	I _{PPM}	12	А		
Peak pulse power	8/20 µs waveform	P _{PP}	300	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 8	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 15	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GL15T						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	8/20 μs	I _{PPM}	10	Α		
Peak pulse power	8/20 μs waveform	P_PP	300	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 8	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 15	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GL24T						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	8/20 μs	I _{PPM}	5	А		
Peak pulse power	8/20 µs waveform	P _{PP}	300	W		
ECD income to	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 8	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 15	kV		
Operating temperature	Junction temperature	TJ	- 55 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ELECTRICAL CHARACTERISTICS GL05T						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	-	lines
Reverse working voltage	at I _R = 1 μA	V_{RWM}	5	-	-	V
Reverse current	at V _R = 5 V	I _R	-	-	20	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6	-	-	V
Reverse clamping voltage	at I _{PP} = 1 A	W	-	-	9.8	V
	at I _{PP} = 5 A	V _C	-	-	11	V
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	5	-	pF

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Low Capacitance ESD Protection Diodes for High-Speed Data Interfaces

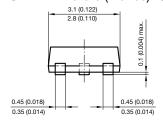
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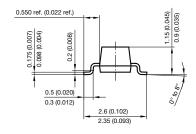
ELECTRICAL CHARACTERISTICS GL12T						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	-	lines
Reverse working voltage	at I _R = 1 μA	V_{RWM}	12	-	-	V
Reverse current	at V _R = 5 V	I _R	-	-	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.3	-	-	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	-	19	V
	at I _{PP} = 5 A	VC	-	-	24	V
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C _D	-	5	-	pF

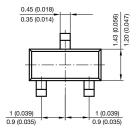
ELECTRICAL CHARACTERISTICS GL15T						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	-	lines
Reverse working voltage	at I _R = 1 μA	V_{RWM}	15	-	-	V
Reverse current	at V _R = 5 V	I _R	-	=	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.7	-	-	V
Reverse clamping voltage	at I _{PP} = 1 A	V	-	-	24	V
	at I _{PP} = 5 A	V _C	=	-	33	V
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	5	-	pF

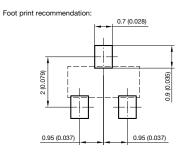
ELECTRICAL CHARACTERISTICS GL24T						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	-	lines
Reverse working voltage	at I _R = 1 μA	V_{RWM}	24	-	-	V
Reverse current	at V _R = 5 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	26.7	-	-	V
Reverse clamping voltage	at I _{PP} = 1 A	V	-	-	43	V
	at I _{PP} = 5 A	- V _C	-	-	55	V
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	-	5	-	pF

PACKAGE DIMENSIONS in millimeters (inches): SOT-23









Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23.Sept.2009

Document Number: 85809 Rev. 1.7, 22-Jul-10



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Document Number: 91000 Revision: 18-Jul-08

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